

## Features

- Pin and function compatible with CY7C1049CV33
- High speed
  - $t_{AA} = 10 \text{ ns}$
- Low active power
  - $I_{CC} = 90 \text{ mA @ } 10 \text{ ns (Industrial)}$
- Low CMOS standby power
  - $I_{SB2} = 10 \text{ mA}$
- 2.0V data retention
- Automatic power down when deselected
- TTL compatible inputs and outputs
- Easy memory expansion with  $\overline{CE}$  and  $\overline{OE}$  features
- Available in Pb-free 36-pin (400 Mil) Molded SOJ and 44-pin TSOP II packages

## Functional Description

The CY7C1049DV33 is a high performance CMOS Static RAM organized as 512K words by 8-bits. Easy memory expansion is provided by an Active LOW Chip Enable ( $\overline{CE}$ ), an Active LOW Output Enable ( $\overline{OE}$ ), and tri-state drivers. You can write to the device by taking Chip Enable ( $\overline{CE}$ ) and Write Enable ( $\overline{WE}$ ) inputs LOW. Data on the eight IO pins ( $IO_0$  through  $IO_7$ ) is then written into the location specified on the address pins ( $A_0$  through  $A_{18}$ ).

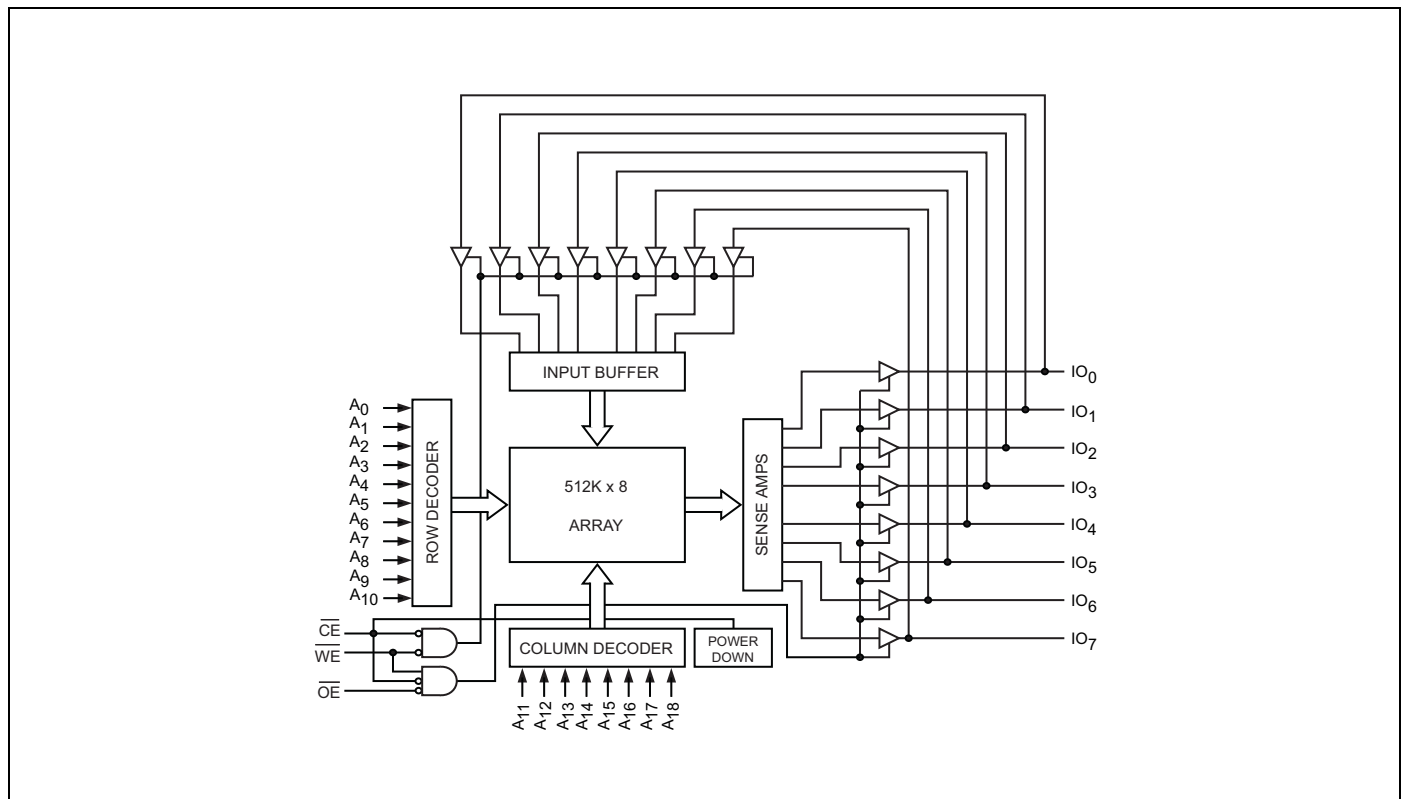
You can read from the device by taking Chip Enable ( $\overline{CE}$ ) and Output Enable ( $\overline{OE}$ ) LOW while forcing Write Enable ( $\overline{WE}$ ) HIGH. Under these conditions, the contents of the memory location specified by the address pins appear on the IO pins.

The eight input or output pins ( $IO_0$  through  $IO_7$ ) are placed in a high impedance state when the device is deselected ( $\overline{CE}$  HIGH), the outputs are disabled ( $\overline{OE}$  HIGH), or during a write operation ( $\overline{CE}$  LOW, and  $\overline{WE}$  LOW).

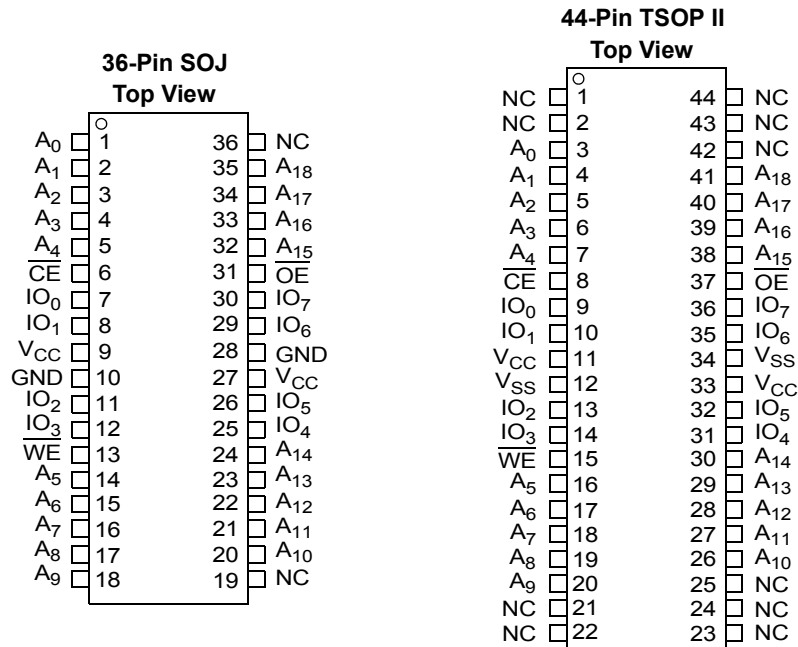
The CY7C1049DV33 is available in standard 400 Mil wide 36-pin SOJ package and 44-pin TSOP II package with center power and ground (revolutionary) pinout.

Refer to the Cypress application note [AN1064, SRAM System Guidelines](#) for best practice recommendations.

## Logic Block Diagram



## Pin Configuration



## Selection Guide

	-10 (Industrial)	-12 (Automotive) <sup>[1]</sup>	Unit
Maximum Access Time	10	12	ns
Maximum Operating Current	90	95	mA
Maximum CMOS Standby Current	10	15	mA

### Note

1. Automotive product information is preliminary.

### Maximum Ratings

Exceeding the maximum ratings may impair the useful life of the device. User guidelines are not tested.

- Storage Temperature ..... -65°C to +150°C
- Ambient Temperature with Power Applied ..... -55°C to +125°C
- Supply Voltage on V<sub>CC</sub> to Relative GND<sup>[2]</sup> ..... -0.3V to +4.6V
- DC Voltage Applied to Outputs in High Z State<sup>[2]</sup> ..... -0.3V to V<sub>CC</sub> + 0.3V
- DC Input Voltage<sup>[2]</sup> ..... -0.3V to V<sub>CC</sub> + 0.3V

- Current into Outputs (LOW)..... 20 mA
- Static Discharge Voltage..... >2001V (MIL-STD-883, Method 3015)
- Latch up Current..... >200 mA

### Operating Range

Range	Ambient Temperature	V <sub>CC</sub>	Speed
Industrial	-40°C to +85°C	3.3V ± 0.3V	10 ns
Automotive	-40°C to +125°C	3.3V ± 0.3V	12 ns

### Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	-10 (Industrial)		-12 (Automotive)		Unit
			Min	Max	Min	Max	
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> = Min, I <sub>OH</sub> = -4.0 mA	2.4		2.4		V
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = Min, I <sub>OL</sub> = 8.0 mA		0.4		0.4	V
V <sub>IH</sub> <sup>[2]</sup>	Input HIGH Voltage		2.0	V <sub>CC</sub> + 0.3	2.0	V <sub>CC</sub> + 0.3	V
V <sub>IL</sub> <sup>[2]</sup>	Input LOW Voltage <sup>[2]</sup>		-0.3	0.8	-0.3	0.8	V
I <sub>IX</sub>	Input Leakage Current	GND ≤ V <sub>I</sub> ≤ V <sub>CC</sub>	-1	+1	-1	+1	µA
I <sub>OZ</sub>	Output Leakage Current	GND ≤ V <sub>OUT</sub> ≤ V <sub>CC</sub> , Output Disabled	-1	+1	-1	+1	µA
I <sub>CC</sub>	V <sub>CC</sub> Operating Supply Current	V <sub>CC</sub> = Max, f = f <sub>MAX</sub> = 1/t <sub>RC</sub>	100 MHz	90		-	mA
			83 MHz	80		95	mA
			66 MHz	70		85	mA
			40 MHz	60		75	mA
I <sub>SB1</sub>	Automatic CE Power down Current —TTL Inputs	Max V <sub>CC</sub> , $\overline{CE} \geq V_{IH}$ ; V <sub>IN</sub> ≥ V <sub>IH</sub> or V <sub>IN</sub> ≤ V <sub>IL</sub> , f = f <sub>MAX</sub>		20		25	mA
I <sub>SB2</sub>	Automatic CE Power down Current —CMOS Inputs	Max V <sub>CC</sub> , $\overline{CE} \geq V_{CC} - 0.3V$ , V <sub>IN</sub> ≥ V <sub>CC</sub> - 0.3V, or V <sub>IN</sub> ≤ 0.3V, f = 0		10		15	mA

### Capacitance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	Max	Unit
C <sub>IN</sub>	Input Capacitance	T <sub>A</sub> = 25°C, f = 1 MHz, V <sub>CC</sub> = 3.3V	8	pF
C <sub>OUT</sub>	IO Capacitance		8	pF

**Note**  
 2. V<sub>IL</sub> (min.) = -2.0V and V<sub>IH</sub>(max) = V<sub>CC</sub> + 2V for pulse durations of less than 20 ns.

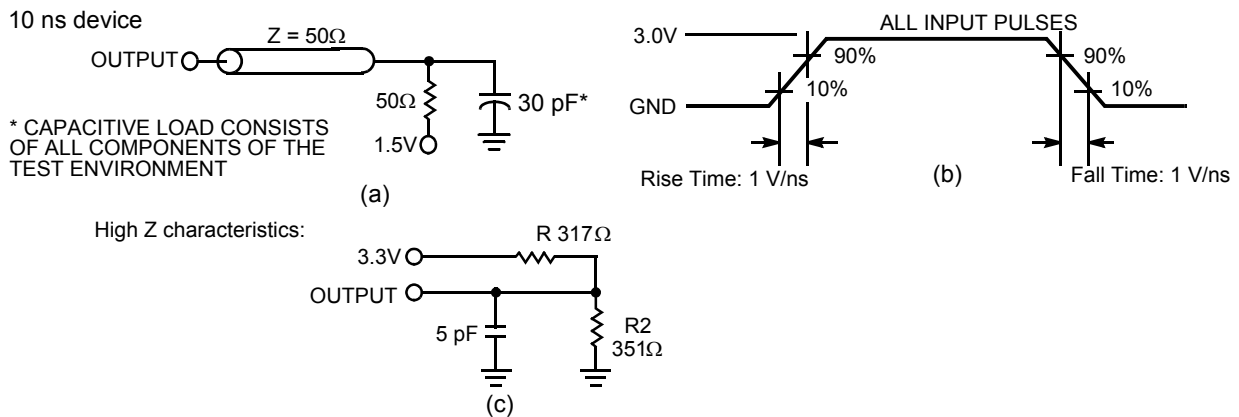
## Thermal Resistance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	SOJ Package	TSOP II Package	Unit
$\Theta_{JA}$	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 × 4.5 inch, two layer printed circuit board	57.91	50.66	°C/W
$\Theta_{JC}$	Thermal Resistance (Junction to Case)		36.73	17.17	°C/W

## AC Test Loads and Waveforms

Figure 1. AC Test Loads and Waveforms [4]

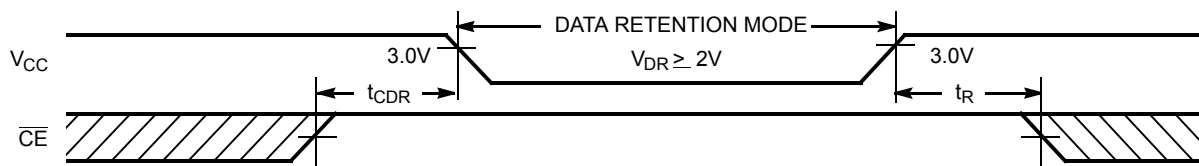


## Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions [5]	Min	Max	Unit
$V_{DR}$	$V_{CC}$ for Data Retention		2.0		V
$I_{CCDR}$	Data Retention Current	$V_{CC} = V_{DR} = 2.0\text{V}$ , $\overline{CE} \geq V_{CC} - 0.3\text{V}$	Ind'l	10	mA
		$V_{IN} \geq V_{CC} - 0.3\text{V}$ or $V_{IN} \leq 0.3\text{V}$	Auto	15	mA
$t_{CDR}^{[3]}$	Chip Deselect to Data Retention Time		0		ns
$t_R^{[6]}$	Operation Recovery Time		$t_{RC}$		ns

Figure 2. Data Retention Waveform



### Note

3. Tested initially and after any design or process changes that may affect these parameters.
4. AC characteristics (except High Z) are tested using the load conditions shown in Figure 1. High Z characteristics are tested for all speeds using the test load shown in Figure (c).
5. No input may exceed  $V_{CC} + 0.3\text{V}$ .
6. Full device operation requires linear  $V_{CC}$  ramp from  $V_{DR}$  to  $V_{CC(min.)} \geq 50\ \mu\text{s}$  or stable at  $V_{CC(min.)} \geq 50\ \mu\text{s}$ .

## AC Switching Characteristics

Over the Operating Range <sup>[7]</sup>

Parameter	Description	-10 (Industrial)		-12 (Automotive)		Unit
		Min	Max	Min	Max	
<b>Read Cycle</b>						
$t_{power}^{[8]}$	$V_{CC}$ (typical) to the first access	100		100		$\mu s$
$t_{RC}$	Read Cycle Time	10		12		ns
$t_{AA}$	Address to Data Valid		10		12	ns
$t_{OHA}$	Data Hold from Address Change	3		3		ns
$t_{ACE}$	$\overline{CE}$ LOW to Data Valid		10		12	ns
$t_{DOE}$	$\overline{OE}$ LOW to Data Valid		5		6	ns
$t_{LZOE}$	$\overline{OE}$ LOW to Low Z	0		0		ns
$t_{HZOE}$	$\overline{OE}$ HIGH to High Z <sup>[9, 10]</sup>		5		6	ns
$t_{LZCE}$	$\overline{CE}$ LOW to Low Z <sup>[10]</sup>	3		3		ns
$t_{HZCE}$	$\overline{CE}$ HIGH to High-Z <sup>[9, 10]</sup>		5		6	ns
$t_{PU}$	$\overline{CE}$ LOW to Power up	0		0		ns
$t_{PD}$	$\overline{CE}$ HIGH to Power down		10		12	ns
<b>Write Cycle<sup>[11, 12]</sup></b>						
$t_{WC}$	Write Cycle Time	10		12		ns
$t_{SCE}$	$\overline{CE}$ LOW to Write End	7		8		ns
$t_{AW}$	Address Set up to Write End	7		8		ns
$t_{HA}$	Address Hold from Write End	0		0		ns
$t_{SA}$	Address Set up to Write Start	0		0		ns
$t_{PWE}$	$\overline{WE}$ Pulse Width	7		8		ns
$t_{SD}$	Data Set up to Write End	5		6		ns
$t_{HD}$	Data Hold from Write End	0		0		ns
$t_{LZWE}$	$\overline{WE}$ HIGH to Low Z <sup>[10]</sup>	3		3		ns
$t_{HZWE}$	$\overline{WE}$ LOW to High Z <sup>[9, 10]</sup>		5		6	ns

### Notes

7. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified  $I_{OL}/I_{OH}$  and 30 pF load capacitance.
8.  $t_{POWER}$  gives the minimum amount of time that the power supply must be at stable, typical  $V_{CC}$  values until the first memory access is performed.
9.  $t_{HZOE}$ ,  $t_{HZCE}$ , and  $t_{HZWE}$  are specified with a load capacitance of 5 pF as in part (d) of AC Test Loads. Transition is measured when the outputs enter a high impedance state.
10. At any temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$ ,  $t_{HZOE}$  is less than  $t_{LZOE}$ , and  $t_{HZWE}$  is less than  $t_{LZWE}$  for any given device.
11. The internal write time of the memory is defined by the overlap of  $\overline{CE}$  LOW, and  $\overline{WE}$  LOW.  $\overline{CE}$  and  $\overline{WE}$  must be LOW to initiate a write, and the transition of either of these signals can terminate the write. The input data set up and hold timing must be referred to the leading edge of the signal that terminates the write.
12. The minimum write cycle time for Write Cycle No. 2 ( $\overline{WE}$  controlled,  $\overline{OE}$  LOW) is the sum of  $t_{HZWE}$  and  $t_{SD}$ .

### Switching Waveforms

Figure 3. Read Cycle No. 1<sup>[13, 14]</sup>

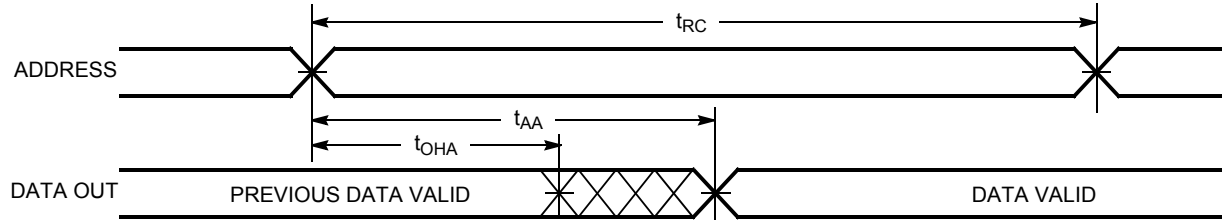


Figure 4. Read Cycle No. 2 ( $\overline{OE}$  Controlled)<sup>[14, 15]</sup>

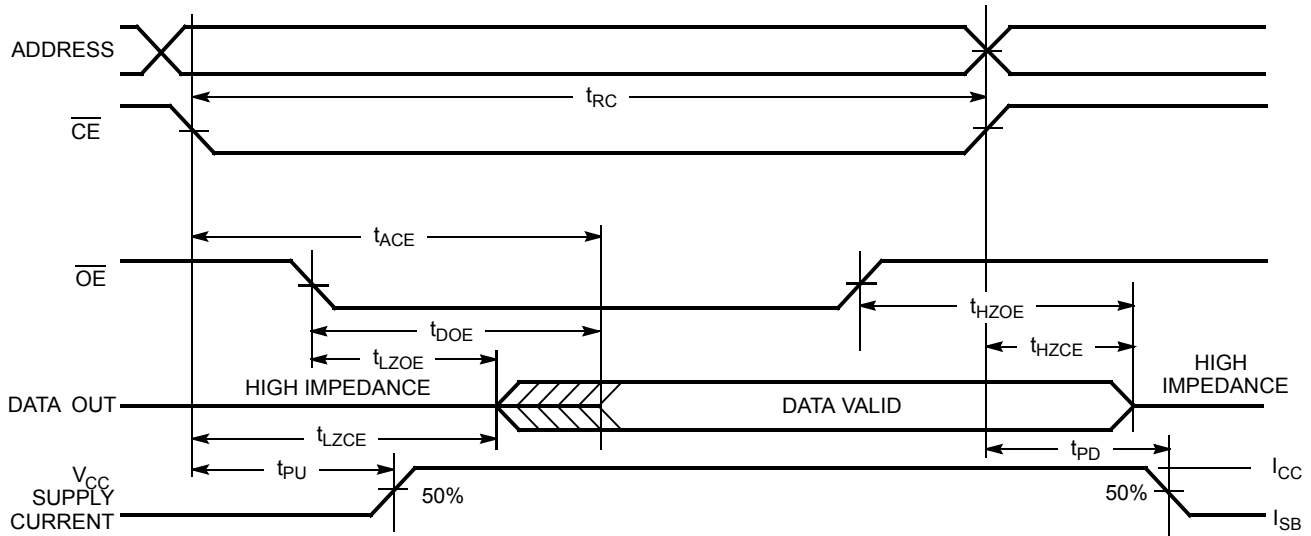
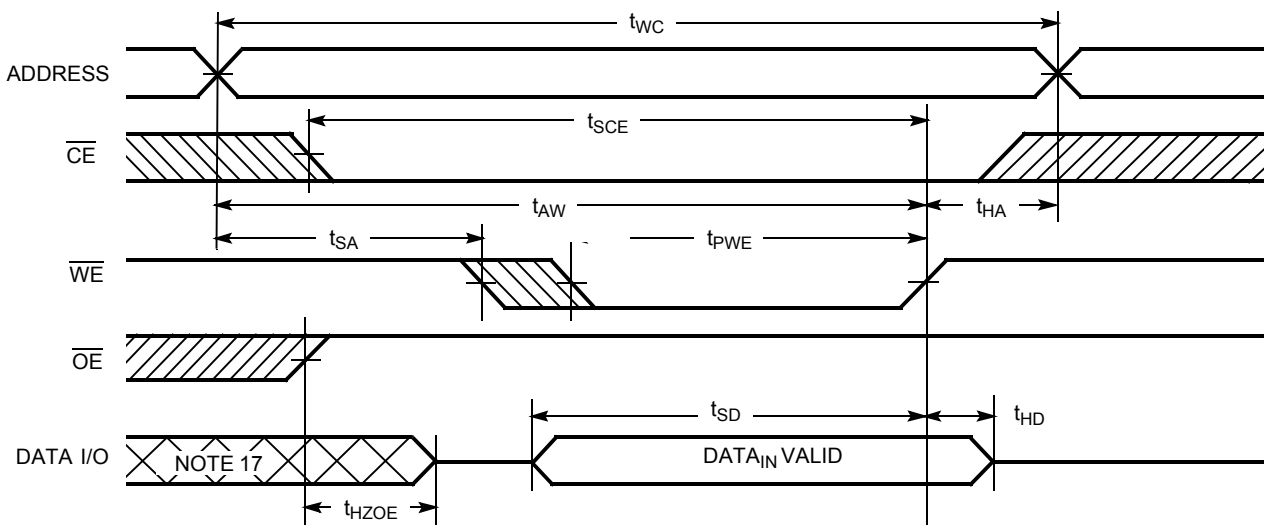


Figure 5. Write Cycle No. 1 ( $\overline{WE}$  Controlled,  $\overline{OE}$  HIGH During Write)<sup>[16, 17]</sup>



**Notes**

- 13. Device is continuously selected.  $\overline{OE}, \overline{CE} = V_{IL}$ .
- 14.  $\overline{WE}$  is HIGH for read cycle.
- 15. Address valid prior to or coincident with  $\overline{CE}$  transition LOW.
- 16. Data IO is high impedance if  $\overline{OE} = V_{IH}$ .
- 17. If  $\overline{CE}$  goes HIGH simultaneously with  $\overline{WE}$  going HIGH, the output remains in a high impedance state.

Switching Waveforms (continued)

Figure 6. Write Cycle No. 2 ( $\overline{WE}$  Controlled,  $\overline{OE}$  LOW)<sup>[17]</sup>

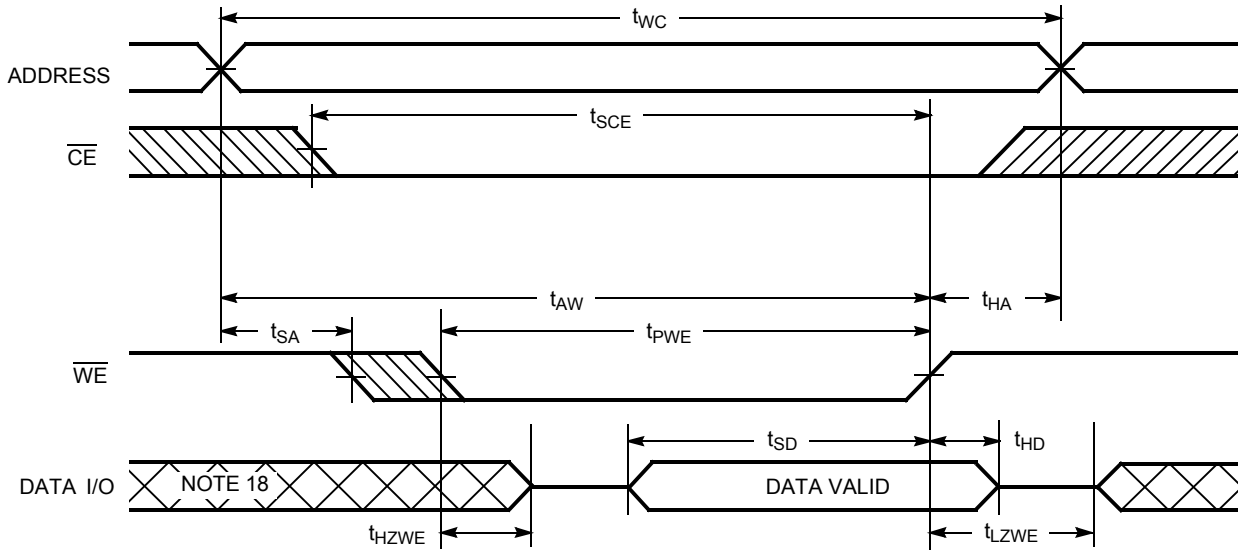
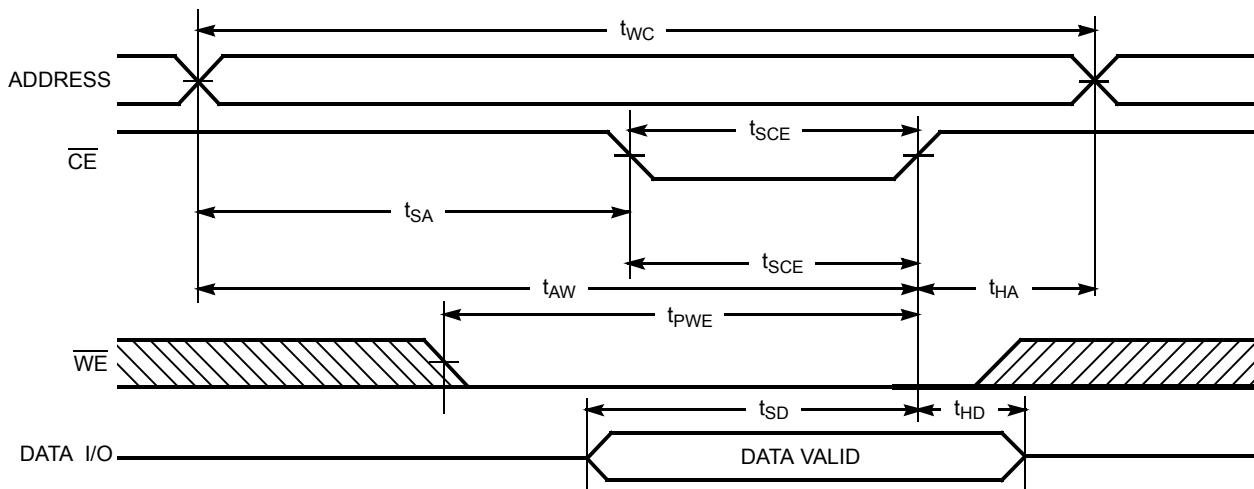


Figure 7. Write Cycle No. 3 ( $\overline{CE}$  Controlled)<sup>[16, 17]</sup>



**Note**  
18. During this period the IOs are in the output state and input signals must not be applied.

**Truth Table**

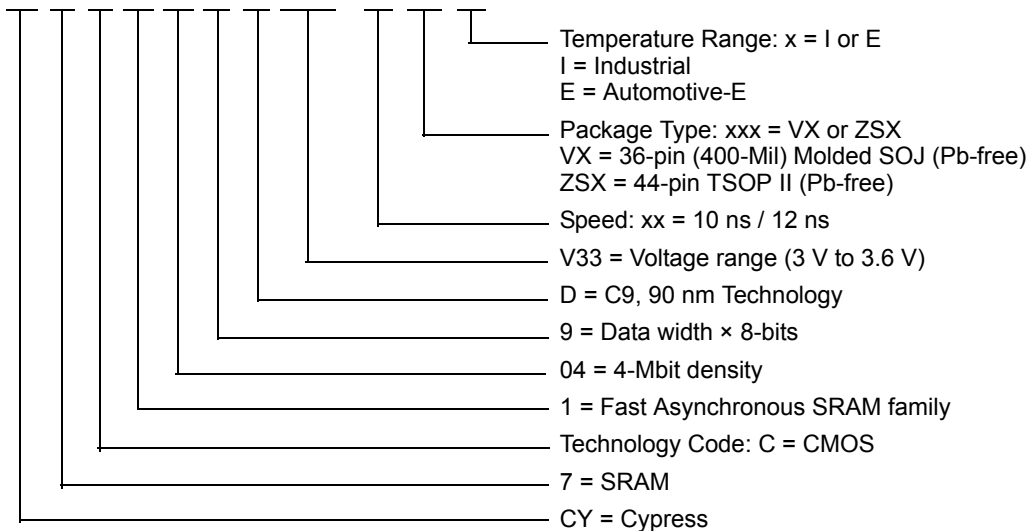
$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	$IO_0$ - $IO_7$	Mode	Power
H	X	X	High Z	Power down	Standby ( $I_{SB}$ )
L	L	H	Data Out	Read	Active ( $I_{CC}$ )
L	X	L	Data In	Write	Active ( $I_{CC}$ )
L	H	H	High Z	Selected, Outputs Disabled	Active ( $I_{CC}$ )

**Ordering Information**

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
10	CY7C1049DV33-10VXI	51-85090	36-pin (400-Mil) Molded SOJ (Pb-free)	Industrial
	CY7C1049DV33-10ZSXI	51-85087	44-pin TSOP II (Pb-free)	
12	CY7C1049DV33-12VXE	51-85090	36-pin (400-Mil) Molded SOJ (Pb-free)	Automotive
	CY7C1049DV33-12ZSXE	51-85087	44-pin TSOP II (Pb-free)	

**Ordering Code Definitions**

CY 7 C 1 04 9 D V33 - XX XXX X

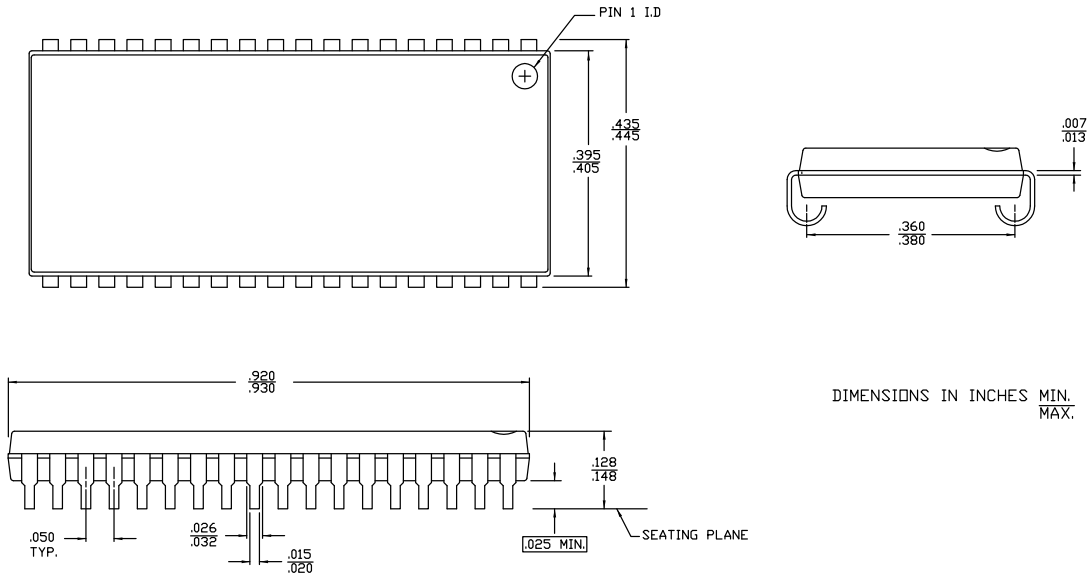


Contact your local Cypress sales representative for availability of these parts.



Package Diagrams

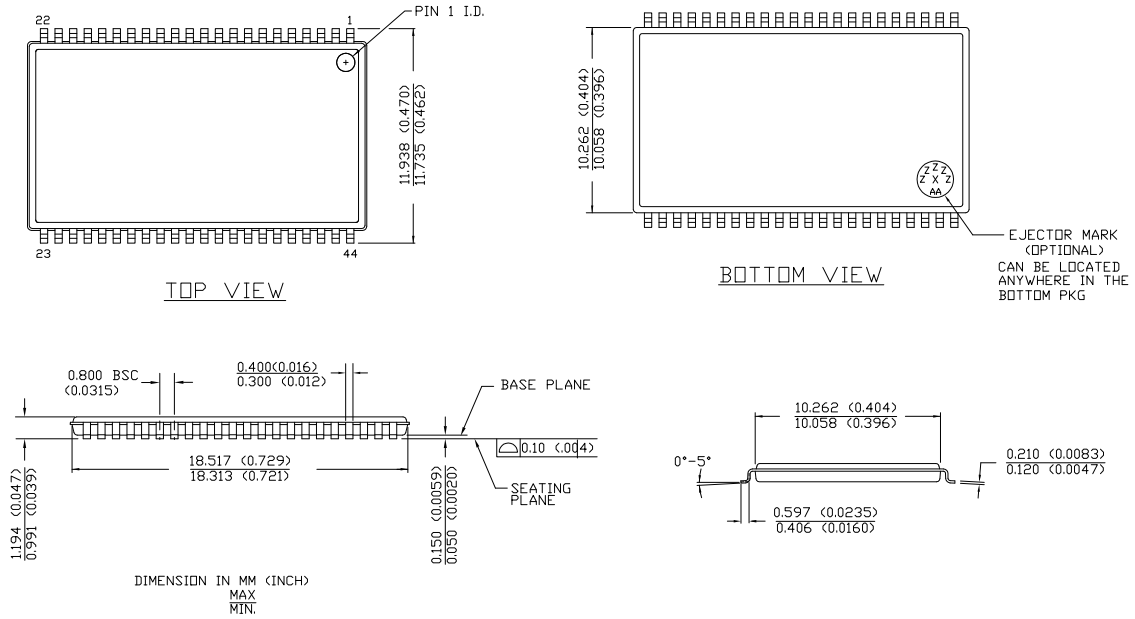
Figure 8. 36-Pin (400-Mil) Molded SOJ (51-85090)



51-85090 \*E

Package Diagrams (continued)

Figure 9. 44-Pin Thin Small Outline Package Type II (51-85087)



51-85087 \*C

Document History Page

Document Title: CY7C1049DV33, 4-Mbit (512K x 8) Static RAM				
Document Number: 38-05475				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	201560	See ECN	SWI	Advance Datasheet for C9 IPP
*A	233729	See ECN	SYT	1.AC, DC parameters are modified as per EROS (Specification # 01-2165) 2.Pb-free offering in the Ordering Information Table
*B	351096	See ECN	PCI	Changed from Advance to Preliminary Removed 20 ns Speed bin Corrected DC voltage (min) value in maximum ratings section from - 0.5 to - 0.3V Redefined I <sub>CC</sub> values for Com'l and Ind'l temperature ranges I <sub>CC</sub> (Com'l): Changed from 100, 80, and 67 mA to 90, 80 and, 75 mA for 8, 10, and 12ns speed bins respectively I <sub>CC</sub> (Ind'l): Changed from 80 and 67 mA to 90 and 85 mA for 10 and 12ns speed bins respectively Added V <sub>IH(max)</sub> specification in Note# 2 Changed reference voltage level for measurement of High Z parameters from ±500 mV to ±200 mV Added Data Retention Characteristics, Waveform, and footnotes 11 and 12 Changed Package Diagram name from 44-pin TSOP II Z44 to 44-pin TSOP II ZS44 Changed part names from Z to ZS in the Ordering Information Table Added 8 ns parts in the Ordering Information Table Added Pb-free Ordering Information Shaded Ordering Information Table
*C	446328	See ECN	NXR	Converted from Preliminary to Final Removed -8 speed bin Removed Commercial Operating Range product information Added Automotive Operating Range product information Updated Thermal Resistance table Updated footnote #8 on High Z parameter measurement Replaced Package Name column with Package Diagram in the Ordering Information table
*D	1274726	See ECN	VKN/AESA	Corrected typo in the 44-Pin TSOP II pinout
*E	2899972	03/29/2010	AJU	Updated <a href="#">Package Diagrams</a> .
*F	3059162	10/14/2010	PRAS	Added <a href="#">Ordering Code Definitions</a> . Updated <a href="#">Package Diagrams</a> .

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